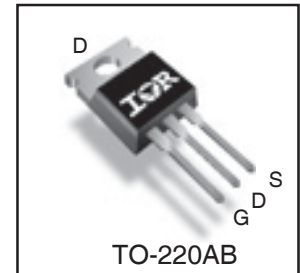
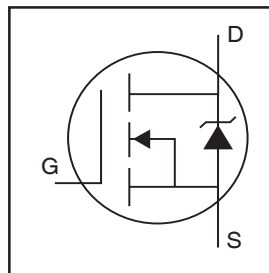


IRFB4227PbF

Features

- Advanced Process Technology
- Key Parameters Optimized for PDP Sustain, Energy Recovery and Pass Switch Applications
- Low E_{PULSE} Rating to Reduce Power Dissipation in PDP Sustain, Energy Recovery and Pass Switch Applications
- Low Q_G for Fast Response
- High Repetitive Peak Current Capability for Reliable Operation
- Short Fall & Rise Times for Fast Switching
- 175°C Operating Junction Temperature for Improved Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability
- Class-D Audio Amplifier 300W-500W (Half-bridge)

Key Parameters		
V_{DS} max	200	V
V_{DS} (Avalanche) typ.	240	V
$R_{DS(ON)}$ typ. @ 10V	19.7	mΩ
I_{RP} max @ $T_C = 100^\circ\text{C}$	130	A
T_J max	175	°C



G	D	S
Gate	Drain	Source

Description

This HEXFET® Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low E_{PULSE} rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	±30	V
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	65	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	46	
I_{DM}	Pulsed Drain Current ①	260	
I_{RP} @ $T_C = 100^\circ\text{C}$	Repetitive Peak Current ⑤	130	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	330	W
P_D @ $T_C = 100^\circ\text{C}$	Power Dissipation	190	
	Linear Derating Factor	2.2	W/°C
T_J	Operating Junction and	-40 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature for 10 seconds	300	
	Mounting Torque, 6-32 or M3 Screw	10lb·in (1.1N·m)	N

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.45	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ④	—	62	

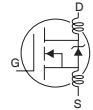
Notes ① through ⑥ are on page 8

IRFB4227PbF

International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	170	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	19.7	24	mΩ	$V_{GS} = 10V, I_D = 46A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-13	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	1.0	mA	$V_{DS} = 200V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$
g_{fs}	Forward Transconductance	49	—	—	S	$V_{DS} = 25V, I_D = 46A$
Q_g	Total Gate Charge	—	70	98	nC	$V_{DD} = 100V, I_D = 46A, V_{GS} = 10V$ ③
Q_{gd}	Gate-to-Drain Charge	—	23	—	nC	
$t_{d(on)}$	Turn-On Delay Time	—	33	—	ns	$V_{DD} = 100V$
t_r	Rise Time	—	20	—	ns	$I_D = 46A$
$t_{d(off)}$	Turn-Off Delay Time	—	21	—	ns	$R_G = 2.5\Omega$
t_f	Fall Time	—	31	—	ns	$V_{GS} = 10V$ ③
t_{st}	Shoot Through Blocking Time	100	—	—	ns	$V_{DD} = 160V, V_{GS} = 15V, R_G = 4.7\Omega$
E_{PULSE}	Energy per Pulse	—	570	—	μJ	$L = 220nH, C = 0.4\mu F, V_{GS} = 15V$ $V_{DS} = 160V, R_G = 4.7\Omega, T_J = 25^\circ\text{C}$
		—	910	—	μJ	$L = 220nH, C = 0.4\mu F, V_{GS} = 15V$ $V_{DS} = 160V, R_G = 4.7\Omega, T_J = 100^\circ\text{C}$
C_{iss}	Input Capacitance	—	4600	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	460	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	91	—		$f = 1.0MHz,$
$C_{oss\ eff.}$	Effective Output Capacitance	—	360	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 160V$
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		

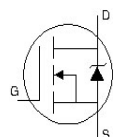


Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	140	mJ
E_{AR}	Repetitive Avalanche Energy ①	—	33	mJ
$V_{DS(Avalanche)}$	Repetitive Avalanche Voltage ①	240	—	V
I_{AS}	Avalanche Current ②	—	39	A

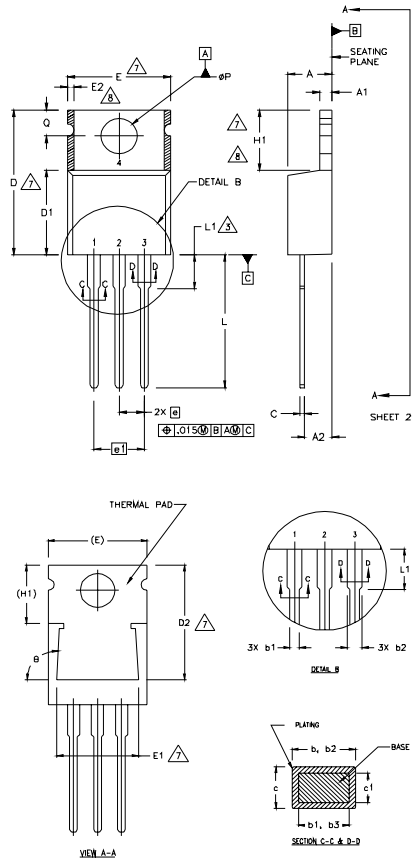
Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	65	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	260		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 46A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	100	150	ns	$T_J = 25^\circ\text{C}, I_F = 46A, V_{DD} = 50V$
Q_{rr}	Reverse Recovery Charge	—	430	640	nC	$di/dt = 100A/\mu s$ ③



IRFB4227PbF

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION : INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

- HEXFET**
- 1- GATE
 - 2- DRAIN
 - 3- SOURCE

IGBTs, CoPACK

- 1- GATE
- 2- COLLECTOR
- 3- EMITTER

DIODES

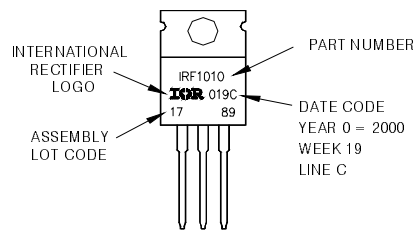
- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°-93°		90°-93°		

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE 'C'

Note: 'P' in assembly line position
indicates 'Lead - Free'



TO-220AB packages are not recommended for Surface Mount Application.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.18\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 39\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ Half sine wave with duty cycle = 0.25, $t_{on} = 1\mu\text{sec}$.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.